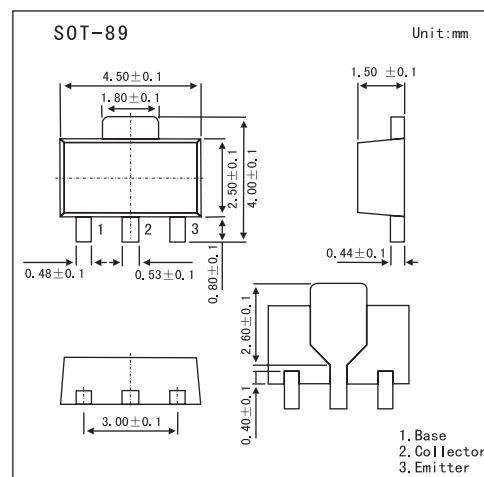


Small Signal Transistor

2SC3439

■ Features

- High h_{FE} =400 to 1800.
- High collector current ($I_{CM}=3A, I_C=1.5A$)
- High collector dissipation $P_C=500mW$
- Low $V_{CE(sat)}$ $V_{CE(sat)}=0.2V$ typ(@ $I_C=1A, I_B=20mA$)
- Small package for mounting.

■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Emitter-base voltage	V_{EBO}	6	V
Collector-emitter voltage	V_{CEO}	25	V
Peak collector current	I_{CM}	3	A
Collector current	I_C	1.5	A
Collector dissipation ($T_a=25^\circ C$)	P_C	500	mW
Junction temperature	T_J	150	$^\circ C$
Storage temperature	T_{stg}	-55 to +150	$^\circ C$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	30			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	6			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, R_{BE}=\infty$	25			V
Collector cutoff current	I_{CBO}	$V_{CB}=20V, I_E=0$			0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB}=2V, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6V, I_C=500mA$	400		1800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1A, I_B=20mA$		0.25	0.5	V
Gain bandwidth product	f_T	$V_{CE}=10V, I_E=-10mA$		130		MHz
Collector output capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1MHz$		17		pF

■ h_{FE} Classification

Marking	HG	HH	HJ
h_{FE}	400~800	600~1200	900~1800